

ON Semiconductor®

BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

General Description

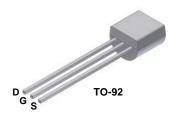
These N-Channel enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

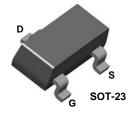
Features

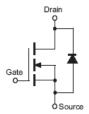
- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.

BS170

MMBF170







Absolute Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units			
V _{DSS}	Drain-Source Voltage	6	V				
V _{DGR}	Drain-Gate Voltage ($R_{GS} \le 1M\Omega$)	1MΩ) 60					
V _{GSS}	Gate-Source Voltage ± 20						
I _D	Drain Current - Continuous	500	500	mA			
	- Pulsed	1200	800	111/			
T _J , T _{STG}	Operating and Storage Temperature Range	- 55 t	°C				
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	30	°C				

Thermal Characteristics $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
P _D	Maximum Power Dissipation Derate above 25°C	830 6.6	300 2.4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	150	417	°C/W

$\textbf{Electrical Characteristics} \quad \textbf{T}_{A} = 25^{\circ} \textbf{C} \text{ unless otherwise noted}$

Symbol	Parameter	Conditions	Туре	Min.	Тур.	Max.	Units
OFF CHA	RACTERISTICS					•	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 100\mu A$	All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	All			0.5	μΑ
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 15V$, $V_{DS} = 0V$	All			10	nA
ON CHAR	RACTERISTICS (Notes 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1mA$	All	8.0	2.1	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 200mA$	All		1.2	5	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	BS170		320		mS
		$V_{DS} \ge 2 V_{DS(on)}$, $I_D = 200 \text{mA}$			320		
Dynamic	Characteristics					•	
C _{iss}	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	All		24	40	pF
C _{oss}	Output Capacitance	f = 1.0MHz	All		17	30	pF
C _{rss}	Reverse Transfer Capacitance		All		7	10	pF
Switching	Characteristics (Notes 1)						
t _{on}	Turn-On Time	$V_{DD} = 25V, I_{D} = 200 \text{mA}, \ V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_{D} = 500 \text{mA},$ $V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	
t _{off}	Turn-Off Time	$V_{DD} = 25V, I_{D} = 200 \text{mA},$ $V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
l		$V_{DD} = 25V, I_D = 500mA,$ $V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	

Note:

Ordering Information

Part Number	Package	Package Type	Lead Frame	Pin array
BS170	TO-92	BULK	STRAIGHT	DGS
BS170-D26Z	TO-92	Tape and Reel	FORMING	DGS
BS170-D27Z	TO-92	Tape and Reel	FORMING	DGS
BS170-D74Z	TO-92	AMMO	FORMING	DGS
BS170-D75Z	TO-92	AMMO	FORMING	DGS
MMBF170	SOT-23	Tape and Reel		

^{1.} Pulse Test: Pulse Width $\leq~300\mu s$, Duty Cycle $\leq~2.0\%$.

Typical Electrical Characteristics

BS170 / MMBF170

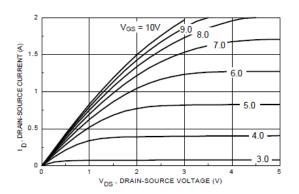


Figure 1. On-Region Characteristics.

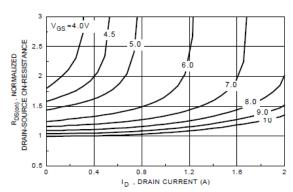


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

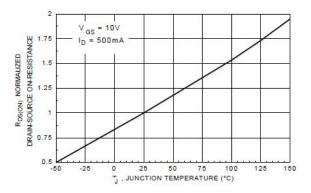


Figure 3. On-Resistance Variation with Temperature.

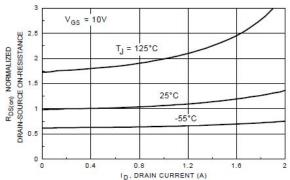


Figure 4. On-Resistance Variation with Drain Current and Temperature.

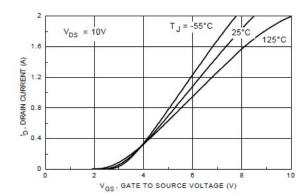


Figure 5. Transfer Characteristics.

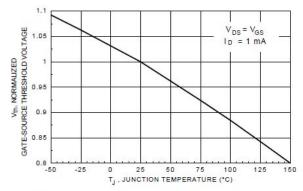


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

BS170 / MMBF170

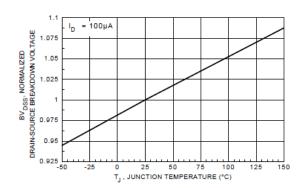


Figure 7. Breakdown Voltage Variation with Temperature.

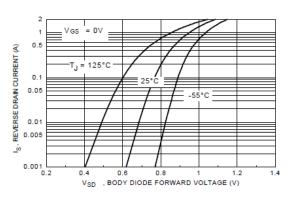


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

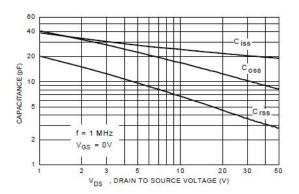


Figure 9. Capacitance Characteristics.

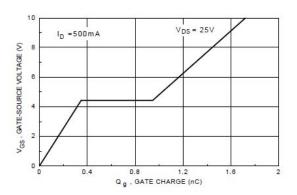


Figure 10. Gate Charge Characteristics.

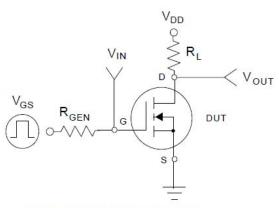


Figure 11. Switching Test Circuit.

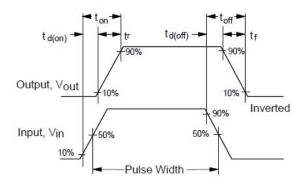
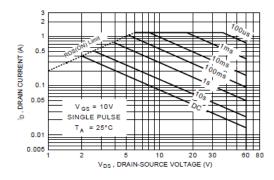


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)



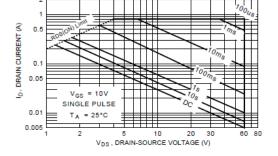


Figure 13. BS170 Maximum Safe Operating Area.

Figure 14. MMBF170 Maximum Safe Operating Area.

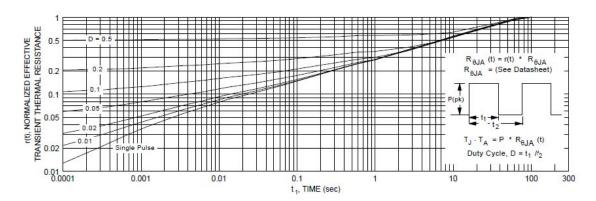


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

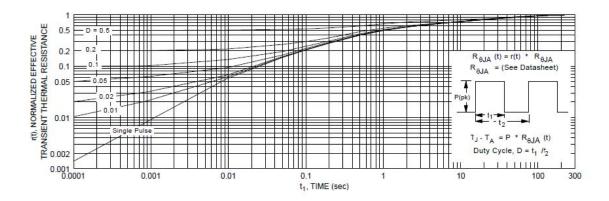
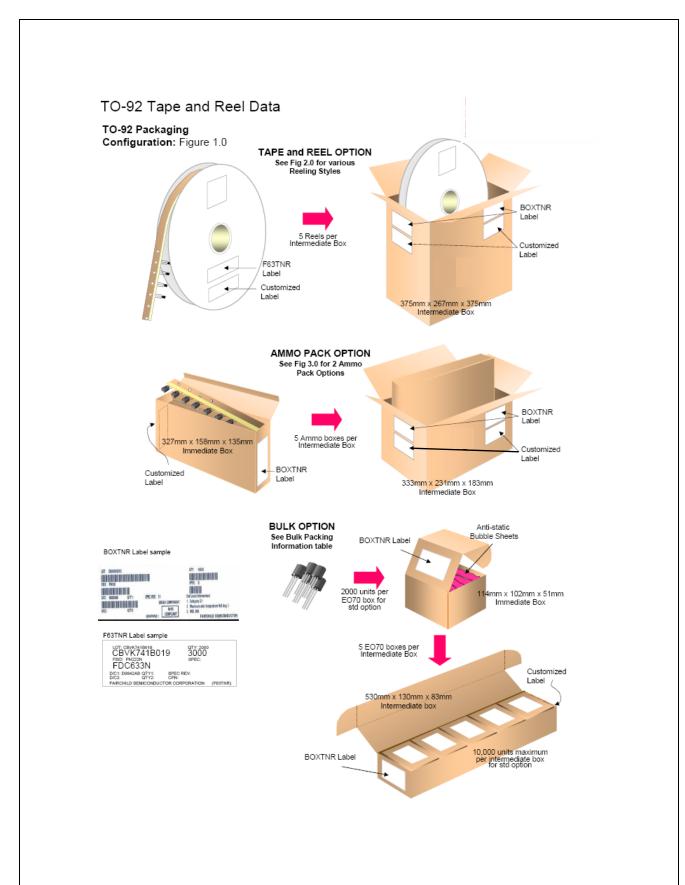


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.



TO-92 Tape and Reel Data, continued

TO-92 Packing

Information: Figure 2.0

TO-92 TNR/AMMO PACKING INFORMATION TABLE

Packing	Style	Quantity	EOL code
Reel	Α	2,000	D26Z
	В	2,000	D11Z
	С	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
	Н	2,000	D89Z
Ammo	М	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm
Reel weight with components = 1.04 kg
Ammo weight with components = 1.02 kg
Max quantity per intermediate box = 10,000 units

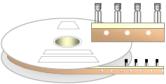
TO-92 BULK PACKING INFORMATION TABLE

EOL CODE /FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OULTINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	-
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0K / BOX	
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	

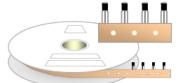
TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 3.0

Machine Option "A" (H)



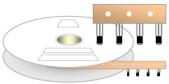
Style "A", D26Z



Style "B", D11Z



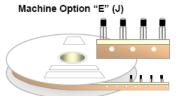
Style "C", D28Z



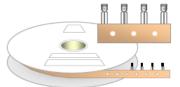
Style "D", D10Z

TO-92 Radial Ammo Packaging Configuration: Figure 4.0

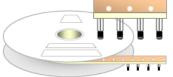




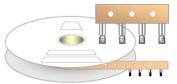
Style "E", D27Z



Style "F", D81Z



Style "G", D29Z

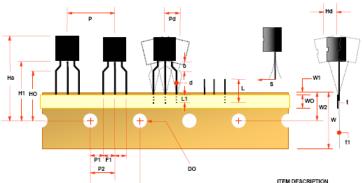


Style "H", D89Z



TO-92 Tape and Reel Data, continued

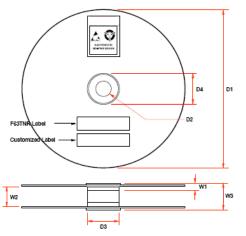
TO-92 Tape and Reel Taping Dimension Configuration: Figure 5.0



User Direction of Feed

TO-92 Reel

Configuration: Figure 6.0



TEM DESCRIPTION	SYMBOL	DIMENSION
lase of Package to Lead Bend	b	0.098 (max)
component Height	Ha	0.928 (+/- 0.025)
ead Clinch Height	HO	0.630 (+/- 0.020)
component Base Height	H1	0.748 (+/- 0.020)
component Alignment (side/side)	Pd	0.040 (max)
component Alignment (front/back)	Hd	0.031 (max)
component Pitch	P	0.500 (+/- 0.020)
eed Hole Pitch	PO	0.500 (+/- 0.008)
lole Center to First Lead	P1	0.150 (+0.009, -0.010)
iale Center to Camponent Center	P2	0.247 (+/- 0.007)
ead Spread	F1/F2	0.104 (+/- 0.010)
ead Thickness	d	0.018 (+0.002, -0.003)
cut Lead Length	L	0.429 (max)
aped Lead Length	L1	0.209 (+0.051, -0.052)
aped Lead Thickness	t	0.032 (+/- 0.006)
arrier Tape Thickness	t1	0.021 (+/- 0.006)
arrier Tape Width	w	0.708 (+0.020, -0.019)
loid - down Tape Width	wo	0.236 (+/- 0.012)
iold - down Tape position	W1	0.035 (max)
eed Hole Position	W2	0.360 (+/- 0.025)
procket Hole Diameter	DO	0.157 (+0.008, -0.007)
ead Spring Out	S	0.004 (max)

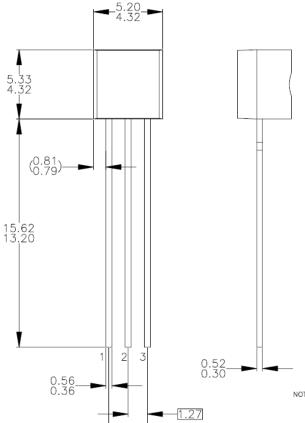
Note : All dimensions are in inches.

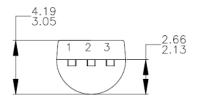
SYMBOL	MINIMUM	MAXIMUM	
D1	13.975	14.025	
D2	1.160	1.200	
D2	0.650	0.700	
D3	3.100	3.300	
D4	2.700	3.100	
W1	0.370	0.570	
W2	1.630	1.690	
W3		2.090	
	D1 D2 D2 D3 D4 W1	D1 13.975 D2 1.160 D2 0.650 D3 3.100 D4 2.700 W1 0.370 W2 1.630	

Note: All dimensions are inches

Mechanical Dimensions (TO-92)

TO-92





2.54

NOTES: UNLESS OTHERWISE SPECIFIED

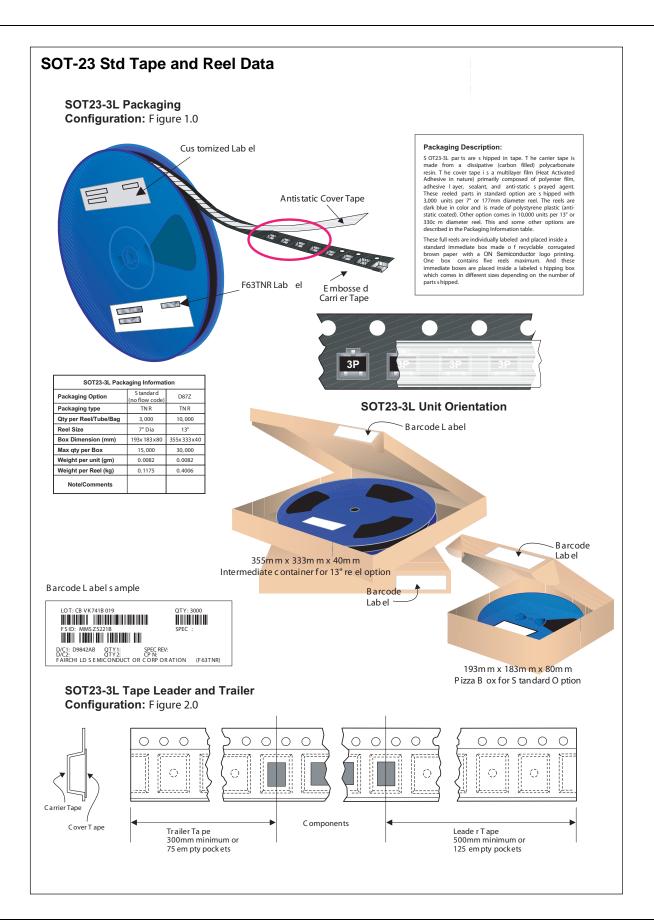
- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS. ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-1994. TO-92 (92,94,96,97,98) PIN CONFIGURATION:

z	92			94			96		97			98			
₫.	Р	F	М	Р	F	М	Р	F	М	Р	F	М	Р	F	М
1	Ε	S	S	Ε	S	S	В	D	G	С	G	D	С	G	D
2	В	D	G	С	G	D	Ε	S	S	В	D	G	Ε	S	S
3	С	G	D	В	D	G	С	G	D	Ε	S	S	В	D	G

LEGEND: P - BIPOLAR F - JFET M - DMOS D - DRAIN S - SOURCE G - GATE E - EMITTER B - BASE C - COLLECTOR

- FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "O" AND SOURCE "S" ARE INTERCHANGEAGLE AT JFET "F" OPTION. DRAWING FILENAME: MKT-ZAO3DREV3. E)

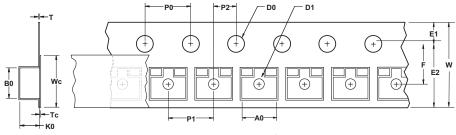
Dimensions in Millimeters



SOT-23 Std Tape and Reel Data, continued

SOT23-3L Embossed Carrier Tape

Configuration: Figure 3.0



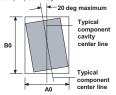
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

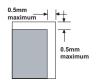
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

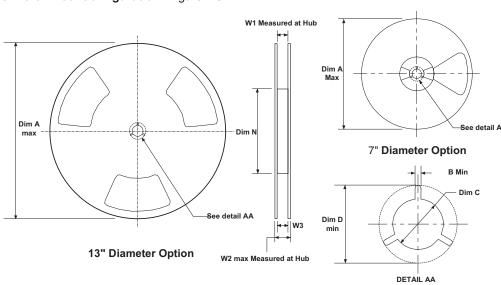


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters											
Tape Size Reel Option Dim A Dim B			Dim C	Dim D Dim N Dim W1		Dim W2	Dim W3 (LSL-USL)					
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9			
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9			

Mechanical Dimensions (SOT-23) SOT-23 0.95 A 2.92±0.20 В 1.40 2.20 2 0.60 0.37 (0.29) --1.00 ⊕ 0.20 M A B 0.95 -1.90 1.90 LAND PATTERN RECOMMENDATION SEE DETAIL A -1.30 MAX 0.10 (0.93)△ 0.10 M C 2.40±0.30 GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS. DIMENSIONING AND TOLERANCING PER ASME Y14.5M — 1994. DRAWING FILE NAME: MAO3DREV9 0.25

0.20 MIN-

(0.55)

DETAIL A

Dimensions in Millimeters

SEATING PLANE

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